

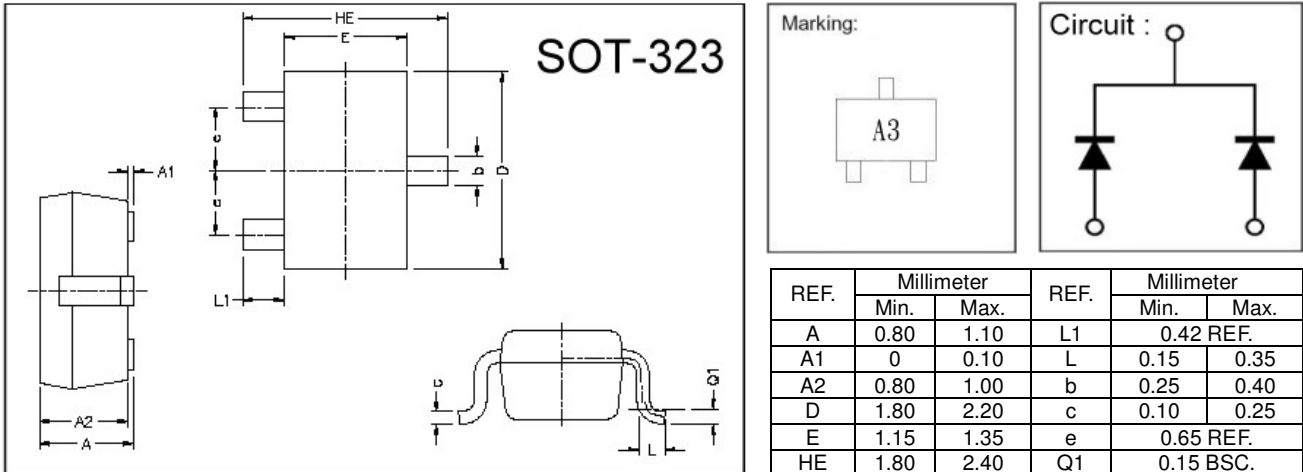
GSN202U

SURFACE MOUNT, SWITCHING DIODE
VOLTAGE 80V, CURRENT 0.1A

Description

The GSN202U is designed for ultra high speed switching.

Package Dimensions



Absolute Maximum Ratings at Ta = 25°C

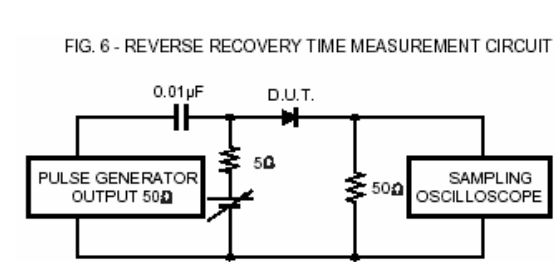
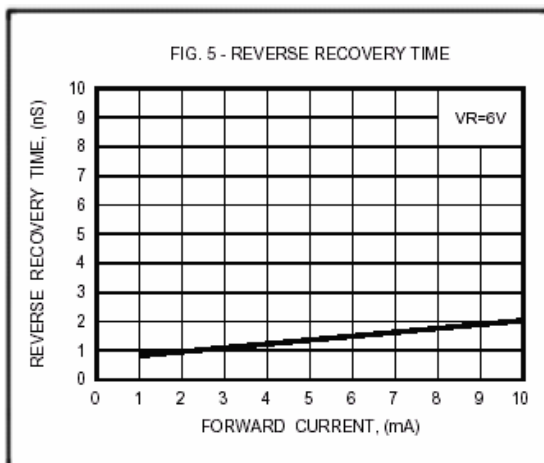
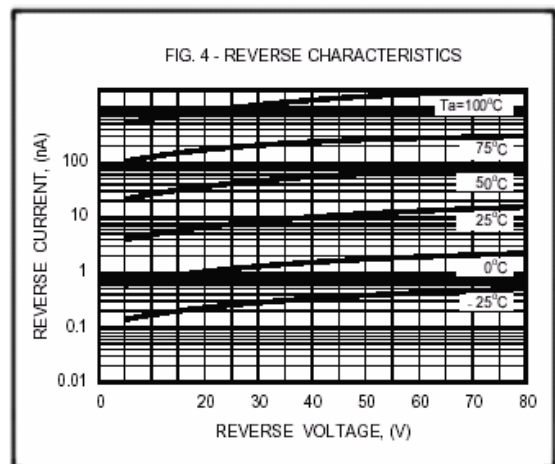
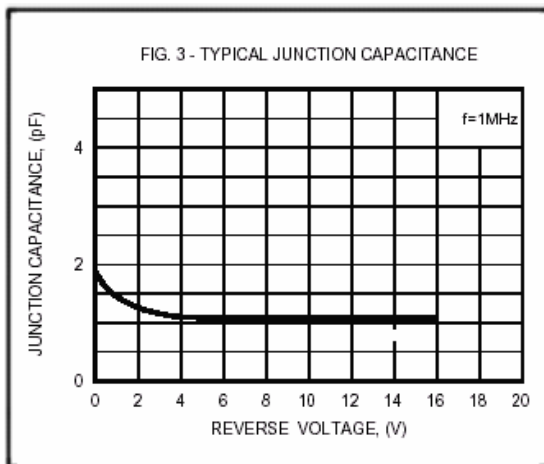
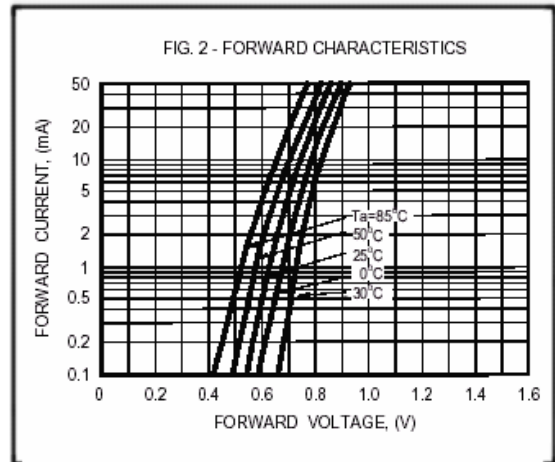
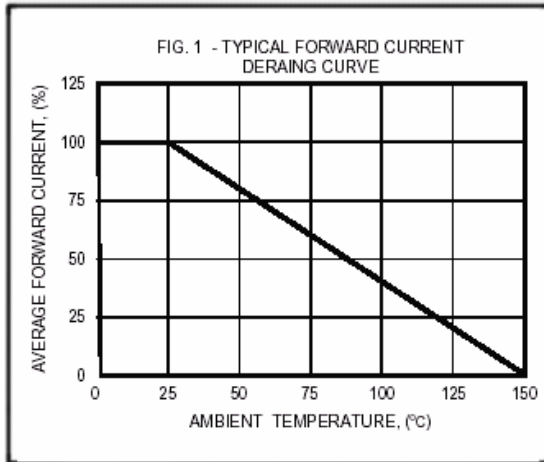
Parameter	Symbol	Ratings	Unit
Junction Temperature	T _J	+150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C
Maximum Peak Repetitive Reverse Voltage	V _{RRM}	80	V
Maximum RMS Voltage	V _{RMS}	56	V
Maximum DC Blocking Voltage	V _{DC}	80	V
Peak Forward Surge Current at 1uSec	I _{FSM}	4.0	A
Typical Junction Capacitance between Terminal (Note 1)	C _J	3.5	pF
Maximum Reverse Recovery Time(Note 2)	T _{RR}	4.0	nSec
Maximum Average Forward Rectified Current	I _o	0.1	A
Total Power Dissipation	PD	225	mW

Characteristics at Ta = 25°C

Characteristics	Symbol	Typ.	Unit	Test Condition
Maximum Instantaneous Forward Voltage	V _F	1.20	V	I _F = 100mA
Maximum Average Reverse Current	I _R	0.1	uA	V _R = 70V

- Notes: 1. Measured at 1.0 MHz and applied reverse voltage of 6.0 volt.
2. Measured at applied forward current of 5mA and reverse voltage of 6.0 volt.
3. ESD sensitive product handling required.

Characteristics Curve



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